

200V N-Ch Power MOSFET

Feature

- ◇ High Speed Power Smooth Switching
- ◇ Enhanced Body diode dv/dt capability
- ◇ Enhanced Avalanche Ruggedness
- ◇ 100% UIS Tested, 100% Rg Tested
- ◇ Lead Free, Halogen Free

Application

- ◇ Synchronous Rectification in SMPS
- ◇ Hard Switching and High Speed Circuit
- ◇ Power Tools
- ◇ UPS
- ◇ Motor Control

V_{DS}		200	V
$R_{DS(on),typ}@V_{GS}=15V$	TO-263	6.4	mΩ
$R_{DS(on),typ}@V_{GS}=10V$	TO-263	6.7	mΩ
$R_{DS(on),typ}@V_{GS}=15V$	TO-247	6.6	mΩ
$R_{DS(on),typ}@V_{GS}=10V$	TO-247	6.9	mΩ
$R_{DS(on),typ}@V_{GS}=15V$	TO-220	6.7	mΩ
$R_{DS(on),typ}@V_{GS}=10V$	TO-220	7	mΩ
I_D		144	A

Part Number	Package	Marking
HIB075N20S5	TO-263	IB075N20S5
HIK075N20S5	TO-247	IK075N20S5
HIP075N20S5	TO-220	IP075N20S5

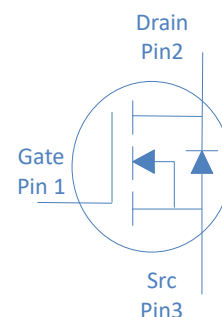
TO-263



TO-220



TO-247



Absolute Maximum Ratings at $T_J=25^{\circ}C$ (unless otherwise specified)

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current	I_D	$T_C=25^{\circ}C$	144	A
		$T_C=100^{\circ}C$	102	
Drain to Source Voltage	V_{DS}	-	200	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	470	A
Avalanche Energy, Single Pulse	E_{AS}	$L=5mH, T_C=25^{\circ}C$	1000	mJ
Power Dissipation	P_D	$T_C=25^{\circ}C$	429	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 175	$^{\circ}C$

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	$R_{\theta JC}$	0.35	$^{\circ}C/W$
Thermal Resistance Junction-Ambient	$R_{\theta JA}$	60	$^{\circ}C/W$

Electrical Characteristics at $T_J=25^{\circ}\text{C}$ (unless otherwise specified)

Static Characteristics

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	200	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	3	3.5	5	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=200V, T_J=25^{\circ}\text{C}$	-	-	1	μA
		$V_{GS}=0V, V_{DS}=200V, T_J=100^{\circ}\text{C}$	-	-	100	
Gate to Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=15V, I_D=20A$ TO-263	-	6.4	7.5	$m\Omega$
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$ TO-263	-	6.7	8.1	$m\Omega$
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=15V, I_D=20A$ TO-247	-	6.6	7.7	$m\Omega$
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$ TO-247	-	6.9	8.3	$m\Omega$
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=15V, I_D=20A$ TO-220	-	6.7	7.8	$m\Omega$
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$ TO-220	-	7	8.4	$m\Omega$
Transconductance	g_{fs}	$V_{DS}=5V, I_D=20A$	-	53	-	S
Gate Resistance	R_G	$V_{GS}=0V, V_{DS}$ Open, $f=1\text{MHz}$	-	1.3	-	Ω

Dynamic Characteristics

Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$	-	3824	-	pF
Output Capacitance	C_{oss}		-	505	-	
Reverse Transfer Capacitance	C_{rss}		-	11	-	
Total Gate Charge	Q_g	$V_{DD}=100V, I_D=20A, V_{GS}=10V$	-	49	-	nC
Gate to Source Charge	Q_{gs}		-	18	-	
Gate to Drain (Miller) Charge	Q_{gd}		-	12	-	
Turn on Delay Time	$t_{d(on)}$	$V_{DD}=100V, I_D=20A, V_{GS}=10V$	-	21	-	ns
Rise time	t_r		-	8	-	
Turn off Delay Time	$t_{d(off)}$		-	27	-	
Fall Time	t_f		-	13	-	

Reverse Diode Characteristics

Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_F=100A$	-	0.85	-	V
Reverse Recovery Time	t_{rr}	$V_R=100V, I_F=20A, dI_F/dt=100A/\mu s$	-	112	-	ns
Reverse Recovery Charge	Q_{rr}		-	461	-	nC

Fig 1. Typical Output Characteristics

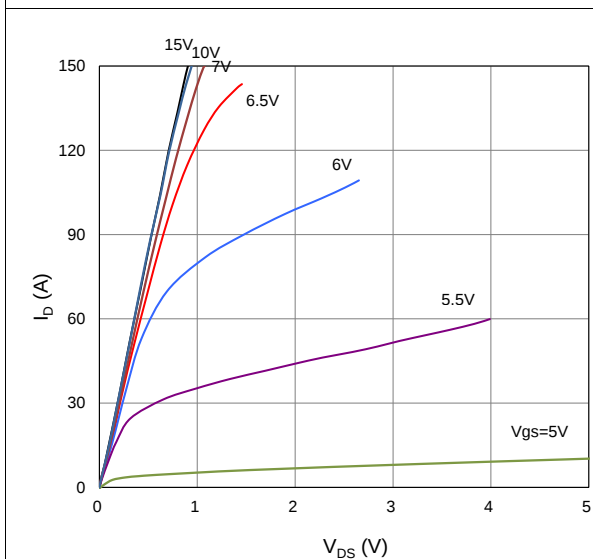


Figure 2. On-Resistance vs. Gate-Source Voltage

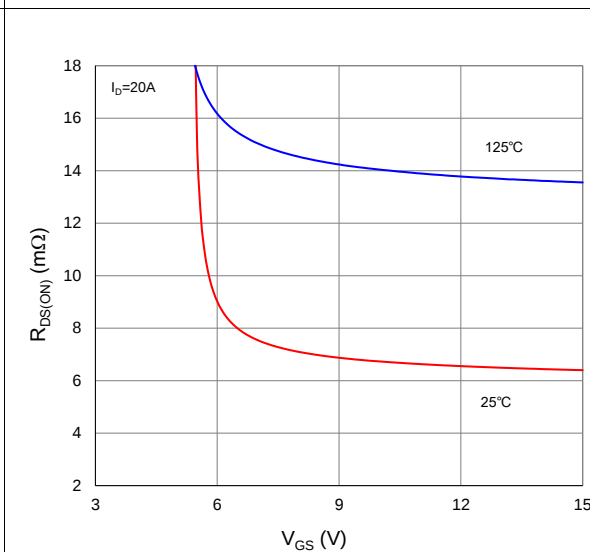


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

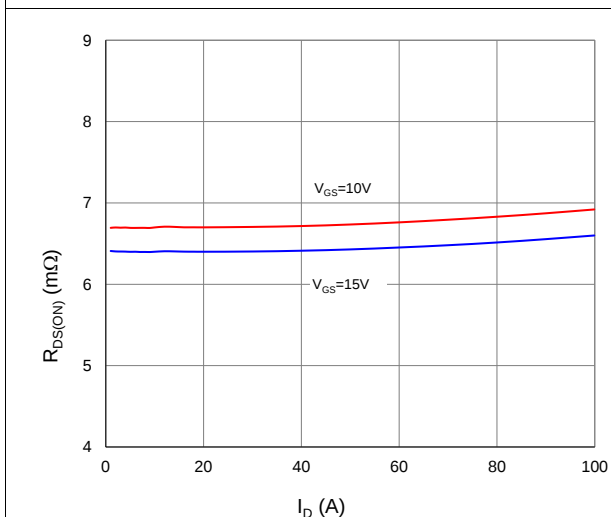


Figure 4. Normalized On-Resistance vs. Junction Temperature

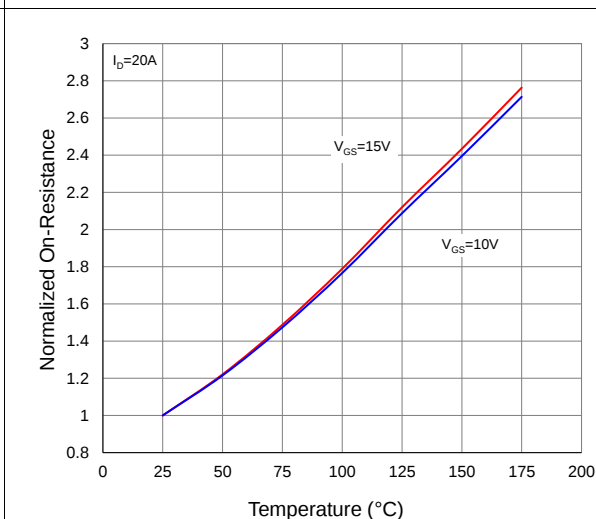


Figure 5. Typical Transfer Characteristics

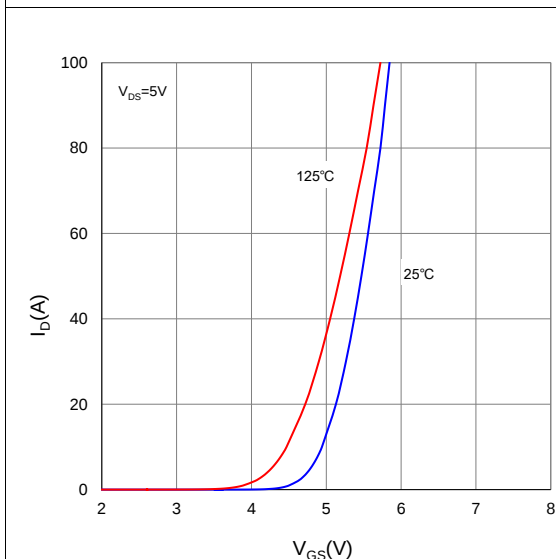


Figure 6. Typical Source-Drain Diode Forward Voltage

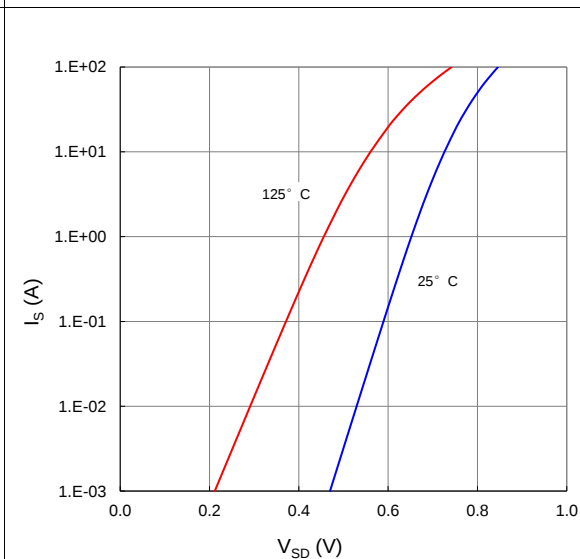


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

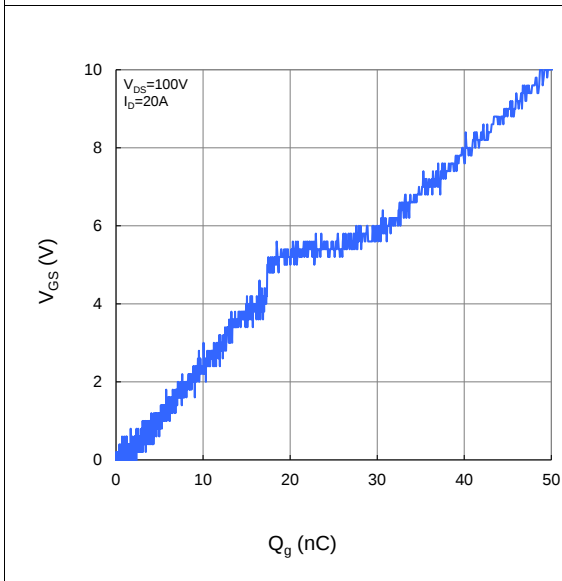


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

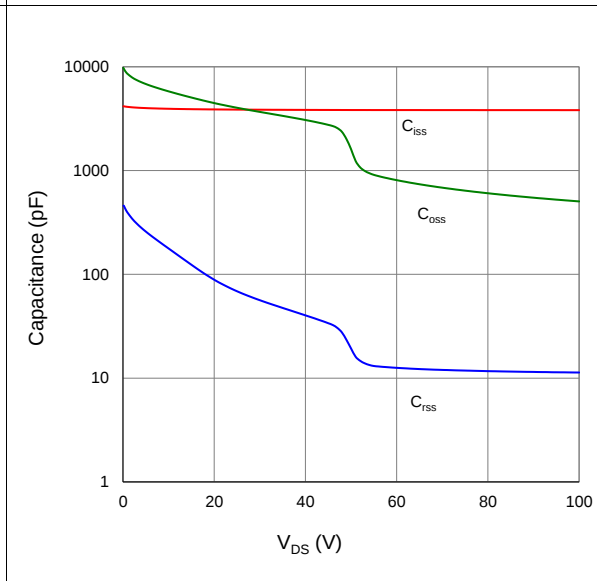


Figure 9. Maximum Safe Operating Area

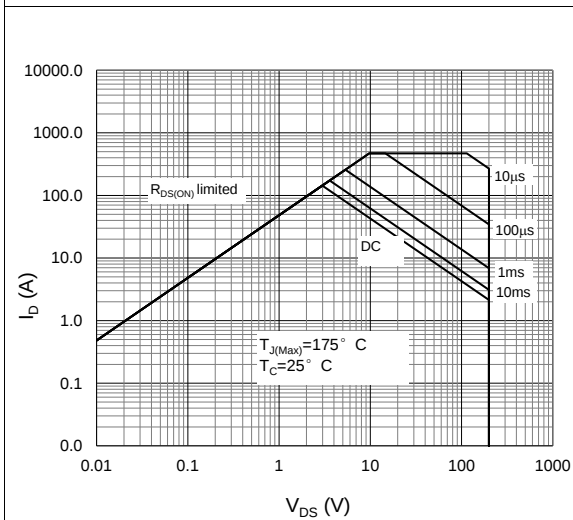


Figure 10. Maximum Drain Current vs. Case Temperature

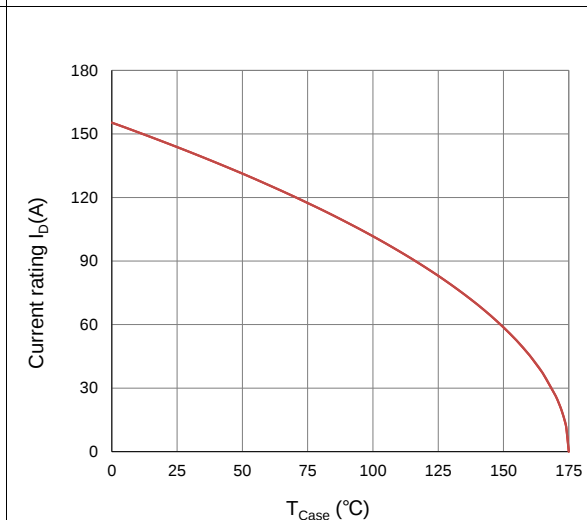
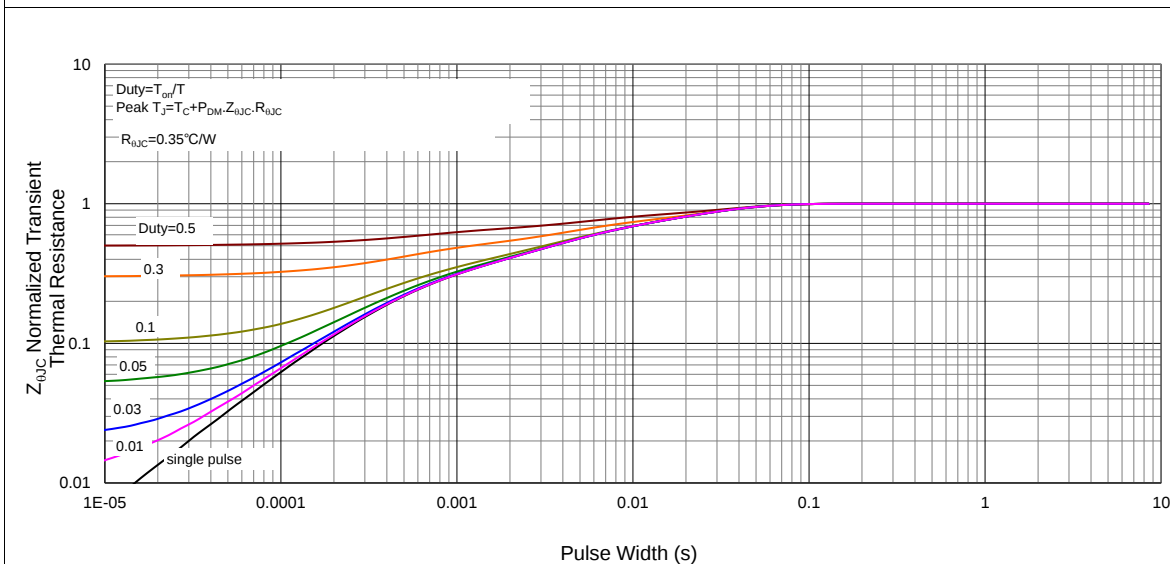
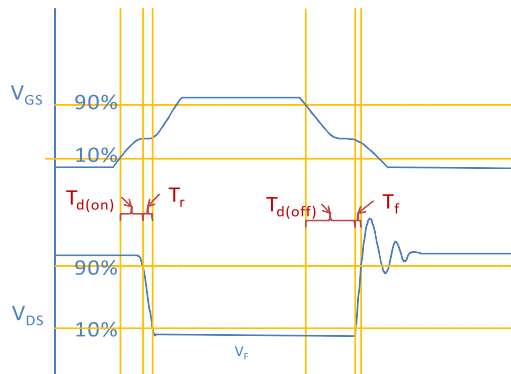
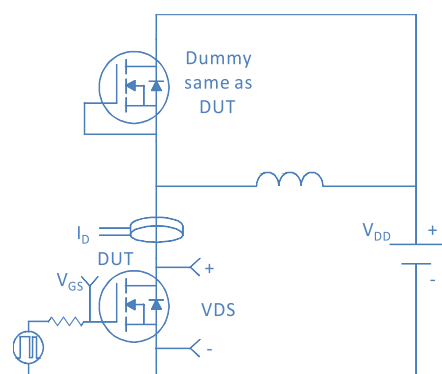


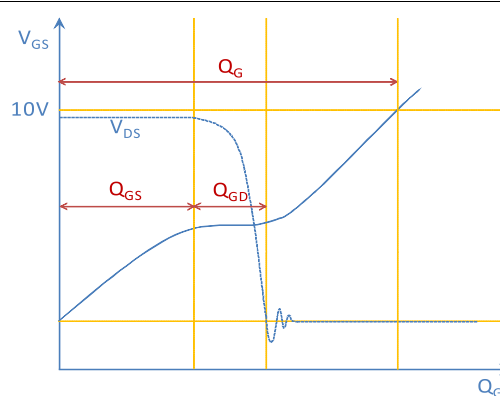
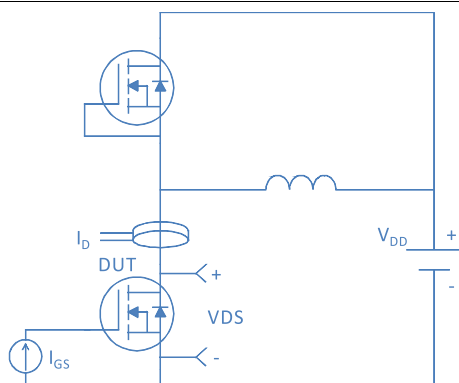
Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Case



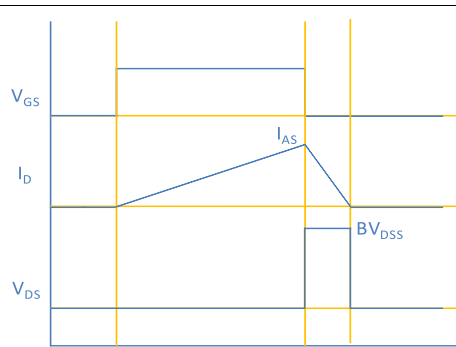
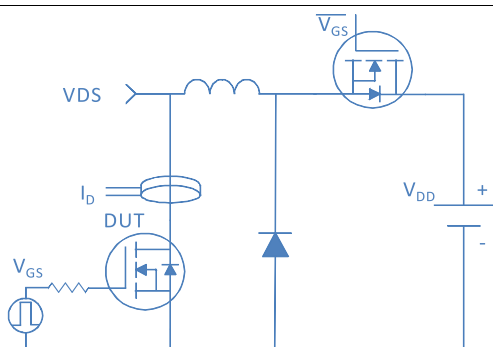
Inductive switching Test



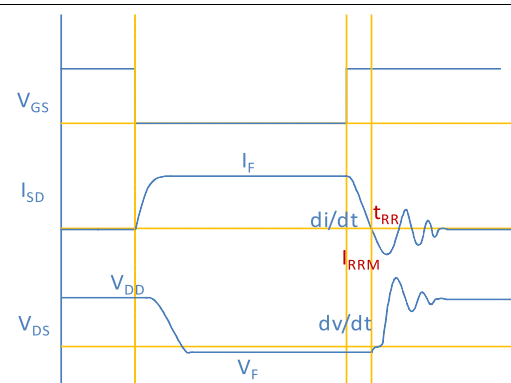
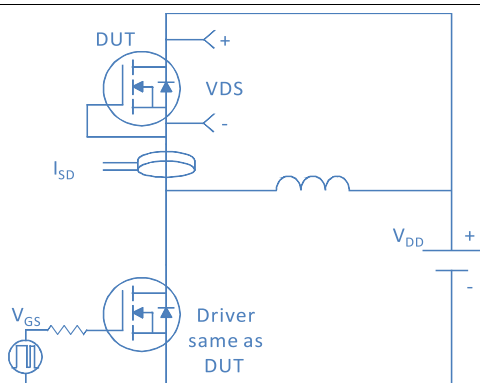
Gate Charge Test

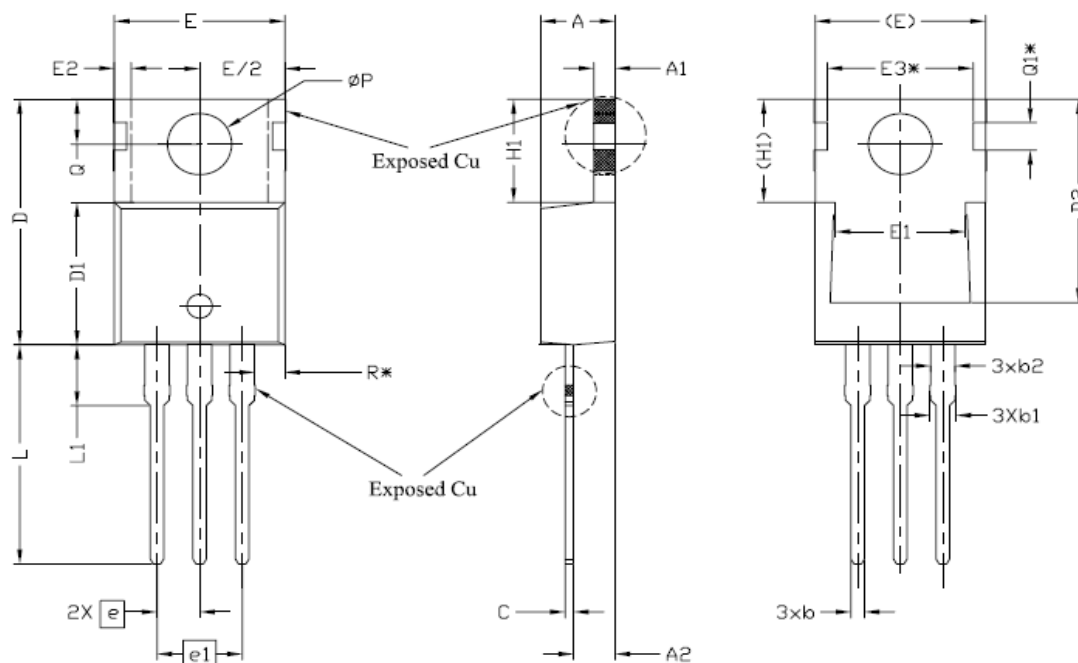


Uclamped Inductive Switching (UIS) Test

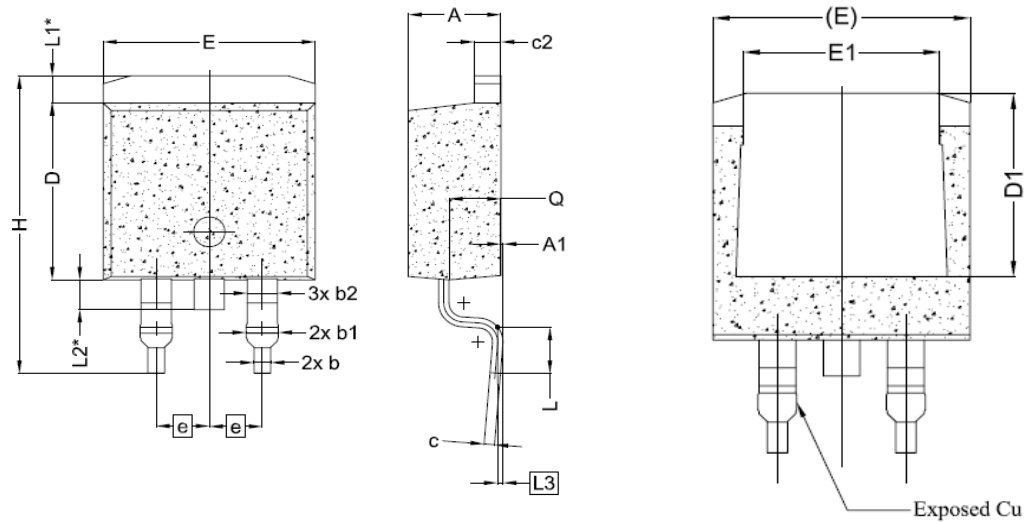


Diode Recovery Test

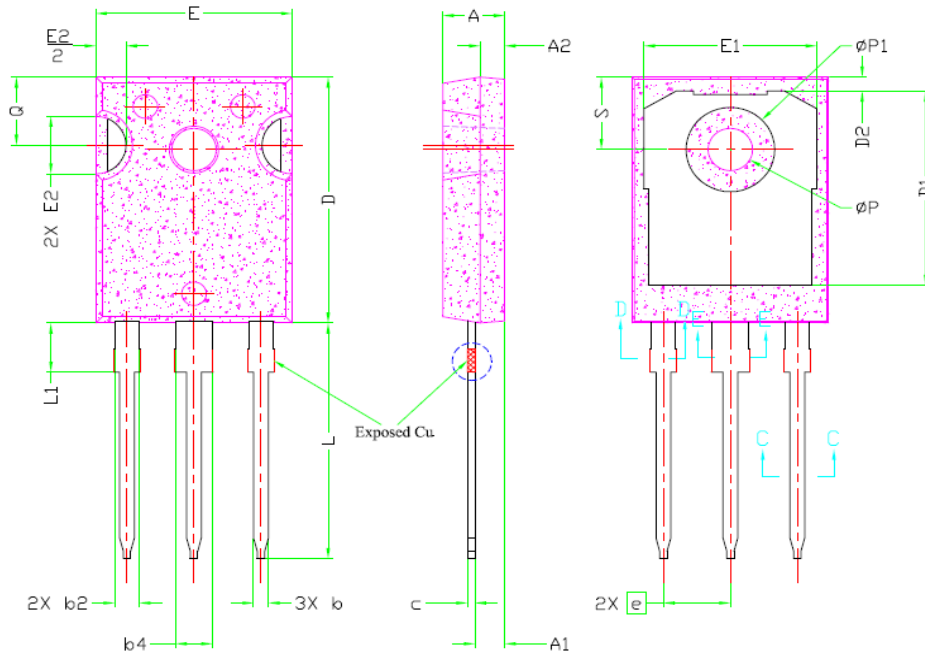


TO-220, 3 leads


SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4,24	4,44	4,64	
A1	1,15	1,27	1,40	
A2	2,30	2,48	2,70	
b	0,70	0,80	0,90	
b1	1,20	1,55	1,75	
b2	1,20	1,45	1,70	
c	0,40	0,50	0,60	
D	14,70	15,37	16,00	4
D1	8,82	8,92	9,02	
D2	12,63	12,73	12,83	5
E	9,96	10,16	10,36	4,5
E1	6,86	7,77	8,89	5
E2	-	-	0,76	6
E3*	8,70REF.			
e	2,54BSC			
e1	5,08BSC			
H1	6,30	6,45	6,60	5,6
L	13,47	13,72	13,97	
L1	3,60	3,80	4,00	
øP	3,75	3,84	3,93	
Q	2,60	2,80	3,00	
Q1*	1,73REF.			
R*	1,82REF.			

TO-263, 2 leads


SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4,24	4,44	4,64
A1	0,00	0,10	0,25
b	0,70	0,80	0,90
b1	1,20	1,55	1,75
b2	1,20	1,45	1,70
c	0,40	0,50	0,60
c2	1,15	1,27	1,40
D	8,82	8,92	9,02
D1	6,86	7,65	—
E	9,96	10,16	10,36
E1	6,89	7,77	7,89
e	2,54 BSC		
H	14,61	15,00	15,88
L	1,78	2,32	2,79
L1	1,36 REF.		
L2	1,50 REF.		
L3	0,25 BSC		
Q	2,30	2,48	2,70

TO-247, 3 leads


SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4,83	5,02	5,21	
A1	2,29	2,41	2,55	
A2	1,50	2,00	2,49	
b	1,12	1,20	1,33	
b1	1,12	1,20	1,28	
b2	1,91	2,00	2,39	6
b3	1,91	2,00	2,34	
b4	2,87	3,00	3,22	6, 8
b5	2,87	3,00	3,18	
c	0,55	0,60	0,69	6
c1	0,55	0,60	0,65	
D	20,80	20,95	21,10	4
D1	16,25	16,55	17,65	5
D2	0,51	1,19	1,35	
E	15,75	15,94	16,13	4
E1	13,46	14,02	14,16	5
E2	4,32	4,91	5,49	3
e	5,44BSC			
L	19,81	20,07	20,32	
L1	4,10	4,19	4,40	6
ØP	3,56	3,61	3,65	7
ØP1	7,19REF.			
Q	5,39	5,79	6,20	
S	6,04	6,17	6,30	